

COMMODORE SEMICONDUCTOR GROUP

a division of Commodore Business Machines, Inc. 950 Rittenhouse Road. Norristown, PA 19403 • 215/666-7950 • TWX 510-660-4168

NMOS

6509 MICROPROCESSOR WITH MEMORY MANAGEMENT

DESCRIPTION

The 6509 is a low-cost microprocessor capable of solving a broad range of small-systems and memory management problems at minimum cost to the user.

A memory management system allows for up to One Mega-Byte of memory for ease in down loading languages, operating systems or other data.

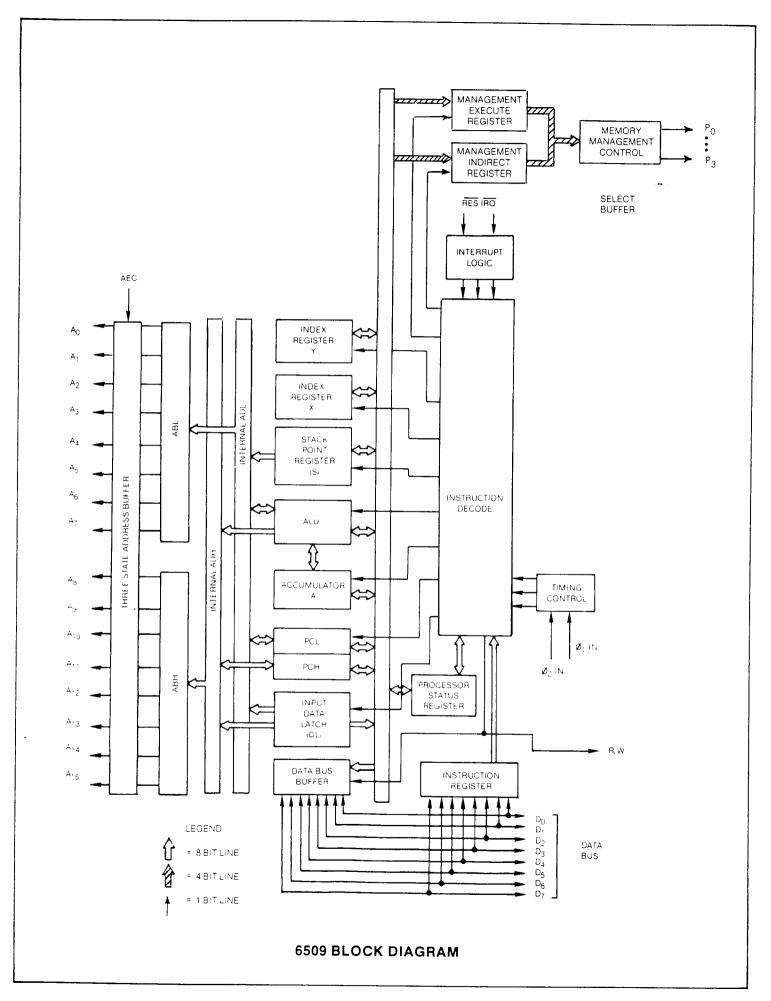
The Three-State sixteen-bit Address Bus allows Direct Memory Accessing (DMA) and multi-processor systems sharing a common memory while the Four-bit Extended Address Register allows for up to one Mega-byte of data storage.

The internal processor architecture is identical to the Commodore Semiconductor Group 6502 to provide software compatibility.

FEATURES OF THE 6509

- Memory management
- On board clock logic
- Addressable memory range of up to 1 M bytes
- Single +5 volt supply
- N channel, silicon gate, depletion load technology
- Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes
- True indexing capability
- Programmable stack pointer
- Variable length stack
- Interrupt capability
- 8 Bit Bi-Directional Data Bus
- Program Addressable memory range of up to 65K bytes
- Direct memory access capability
- Bus compatible with M6800
- Pipeline architecture
- 1 MHz, 2 MHz, and 3 MHz operation
- Use with any type or speed memory

PIN CONFIGURATION READY C ⊐ ø₂IN 40 **IRQ** 2 39 RESET Þ Ø₁ IN SYNC 3 38 NMI ⊂ □ R/W 37 AEC 5 36 **–** D0 **D**1 VDD 6 35 7 **D** D2 Α0 34 **D** D3 Α1 8 33 Α2 9 32 **⊐** D4 10 **D**5 6509 А3 31 d **⊐** D6 A4 11 30 **D**7 Α5 12 29 Α6 13 28 ∍ so 14 **⊐** P0 Α7 ᆸ 27 15 **⊃** P1 A8 🗖 26 Α9 16 25 **P**2 17 **▶** P3 A10 24 A11 d 18 23 **** A15 19 22 □ A14 A12 yss 20 A13 21



6509 CHARACTERISTICS

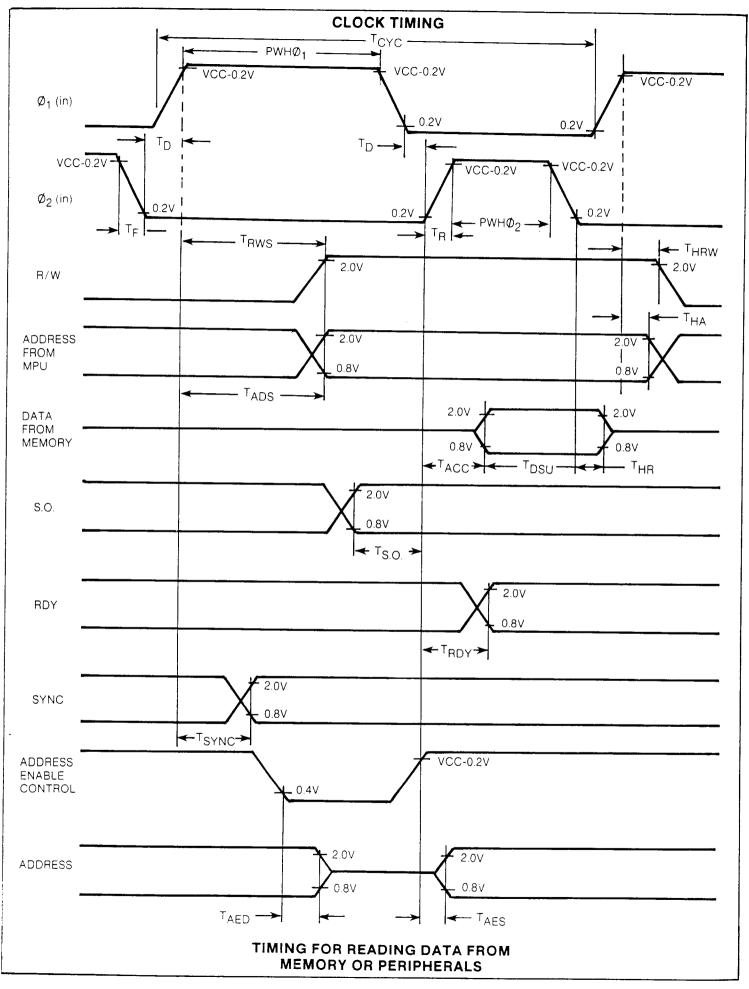
MAXIMUM RATINGS

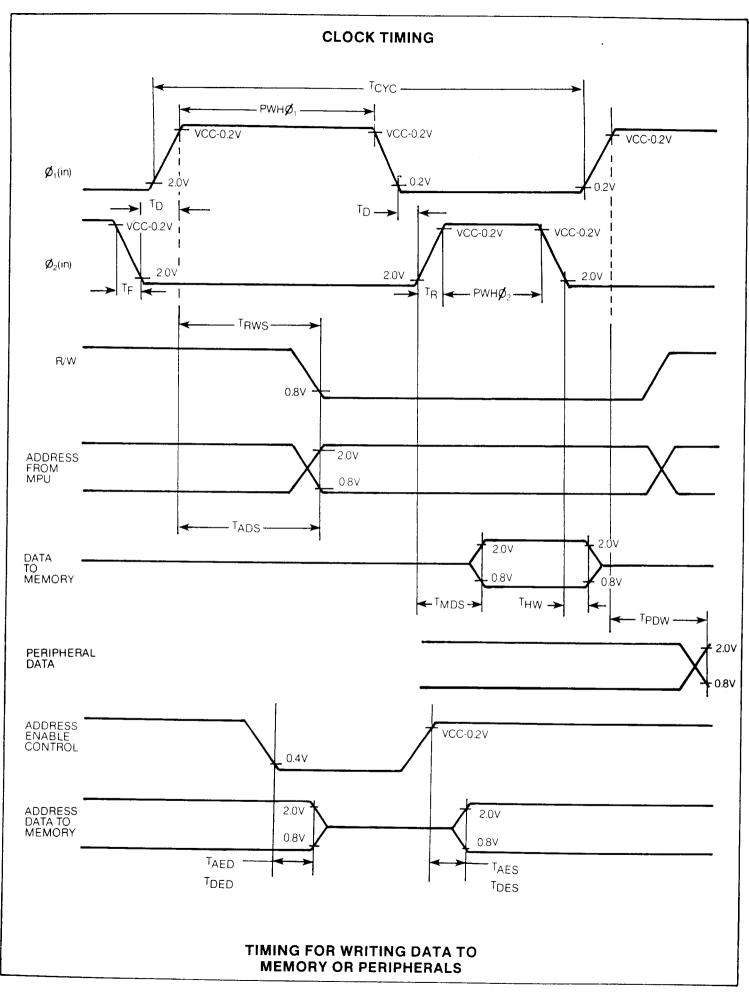
RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	V _{CC}	-0.3 to + 7.0	Vdc
INPUT VOLTAGE	Vin	-0.3 to $+7.0$	Vdc
OPERATING TEMPERATURE	TA	0 to + 70	С
STORAGE TEMPERATURE	TSTG	-55 to + 150	С

This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

ELECTRICAL CHARACTERISTICS (Vcc = 5.0V \pm 5%, Vss = 0, T_A = 0° to + 70°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input High Voltage		SHPALL			
\mathcal{O}_1 , $\mathcal{O}_2(in)$	VIH	Vcc - 0.2	_	Vcc + 1.0V	Vdc
Input High Voltage					
RES, P _ປ -P ₇ IRQ, Data		2.0	-		Vdc
Input Low Voltage					
Ø;, Ø _{2(in)}	VIL	_	_	0.2	Vdc
RES, P ₀ -P ₇ IRQ, Data		_		0.8	Vdc
Input Leakage Current					
$(V_{in} = 0 \text{ to } 5.25V, Vcc = 5.25V)$ Logic	lin			2.5	
$\mathcal{O}_1, \mathcal{O}_2(in)$,,,,	_	_	100	Au, Au,
Three State (Off State) Input Current			 		
$(V_{in} = 0.4 \text{ to } 2.4V, Vcc = 5.25V)$					
Data Lines	ITSI	_	_	· 10	μA
Output High Voltage					
$(I_{OH} = -100 \mu Adc, Vcc = 4.75 V)$ Data, A0-A15, R/W, P ₀ -P ₇	VOH	2.4			Vdc
		2.7		-	Vuc
Out Low Voltage (IOL = 1.6mAdc, Vcc = 4.75V)					
Data, A0-A15, R/W, P ₀ -P ₇	VOL	– .	_	+0.60	Vdc
Power Supply Current	ICC	_	125		mA
Capacitance	С				pF
$V_{in} = 0$, $T_A = 25$ C, $f = 1$ MHz) Logic, P_0 - P_7	C _{in}	_		10	
Data	OIM	_		10	
A0-A15, R/W	C _{out}		_	15 12	
Ø :	C ⊘ ,	_	30	50	
\mathcal{O}_2	C ø ₂	-	50	80	





AC CHARACTERISTICS

1 MHz TIMING

2 MHz TIMING

3 MHz TIMING

ELECTRICAL CHARACTERISTICS (VCC = 5V + 5%, VSS = OV, TA = 0° -70°C)

Clock Timing

CHARACTERISTIC	
Cycle Time	
Clock Pulse Width Ø1 (Measured at VCC - 0 2V) Ø2	
Fall Time, Rise Time (Measured from 0.2V to VCC - 0.2V)	
Delay Time between Clocks (Measured at 0.2V)	

SYMBOL	MIN.	MAX.
TCYC	1000	_
PWHØ ₁ PWHØ ₂	430 470	_ _
TF. TR	-	25
TD	0	

MIN.	MAX
500	_
215 235	_
_	15
0	-

MIN.	MAX	UNITS
333	_	ns
145 165	_ _	ns ns
_	15	ns
0	_	ns

Read/Write Timing (Load = 1 TTL)

CHARACTERISTIC	SYMBOL	MIN.	MAX.	MIN
lead. Write Setup Time from 6509	TRWS	_	300	
ddress Setup Time from 6509	TADS		300	
emory Read Access Time	TACC	_	575	
ata Stability Time Period	TDSU	100	_	50
ata Hold Time-Read	THR	10	_	10
ata Hold Time-Write	THW	10	_	10
Data Setup Time from 6509	TMDS	_	200	_
ddress Hold Time	THA	10	_	10
/W Hold Time	THRW	10	-	10
ort Output Data Valid Memory Management)	T _{PDW}		300	-
RDY Setup Time	TRDY	100		50
.O. Setup Time	Ts.O.	100	_	50
SYNC Setup Time from 6509	TSYNC	_	350	_
Address Enable Setup Time	TAES	_	75	
Data Enable Setup Time	TDES	_	120	
Address Disable *See Note 1	TAED	_	120	
Data Disable *See Note 1	TDED		130	

				_
MIN	MAX.	MIN.	MAX.	UNITS
	150	_	125	ns
_	150	-	125	ns
_	300	_	250	ns
50		50	_	ns
10		10	-	ns
10	_	10	_	ns
-	100		100	ns
10	_	10	_	ns
10	-	10	-	ns
	150		125	ļus
50	-	15		ns
50		50	_	ns
_	175	_	120	ns
_	75	_	75	ns
_	120	-	120	ns
	120	-	120	ns
_	130	_	130	ns

CL = 30pf

SIGNAL DESCRIPTION

Clocks (\$1, \$2)

The 6509 requires a two phase non-overlapping clock that runs at the Vcc voltage level.

Address Bus (A₀-A₁₅)

The tri-state outputs are TTL compatible, capable of driving one standard TTL load and 130 pf.

Data Bus (D₀-D₇)

Eight pins are used for the data bus. This is a Bi-Directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130 pf.

Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line

is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the R/W signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.

^{*}Note 1 — 1TTL Load

Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The microprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses.

Address Enable Control (AEC)

The Address Bus, Data Bus, and R/W signal are valid only when the Address Enable Control line is high. When low, the Address Bus is in a high-impedance state. This feature allows easy DMA and multiprocessor systems.

Read/Write (R/W)

This signal is generated by the microprocessor to control the direction of data transfers on the Data Bus. This line is high except when the microprocessor is writing to memory or a peripheral device.

Ready (RDY)

This input signal allows the user to single cycle the microprocessor on all cycles except write cycles. A negative transition to the low state during or coincident with phase one (\emptyset_1) and up to 100ns after phase two (\emptyset_2) will halt the microprocessor with the output address lines reflecting the current address being fetched. This condition will remain through a subsequent phase two (\emptyset_2) in which the Ready signal is low. This feature allows microprocessor interfacing with low speed PROMS as well as fast (max. 2 cycle) Direct Memory Access (DMA). If Ready is low during a write cycle, it is ignored until the following read operation.

Non-Maskable Interrupt (NMI)

A negative going edge on this input requests that a non-maskable interrupt sequence be generated within the microprocessor.

NMI is an unconditional interrupt. Following completion of the current instruction, the sequence of operations defined for IRQ will be performed, regardless of the interrupt mask flag status. The vector address loaded into the program counter, low and high, are locations FFFA and FFFB respectively, thereby transferring program control to the memory vector located at these addresses. The instructions loaded at these locations cause the microprocessor to branch to a non-maskable interrupt routine in memory.

NMI also requires an external 3K resistor to V_{CC} for proper wire-OR operations.

Inputs $\overline{\text{IRQ}}$ and $\overline{\text{NMI}}$ are hardware interrupt lines that are sampled during \emptyset_2 (phase 2) and will begin the appropriate interrupt routine on the \emptyset_1 (phase 1) following the completion of the current instruction.

Set Overflow Flag (.S.O.)

A NEGATIVE going edge on this input sets the overflow bit in the Status Code Register. This signal is sampled on the trailing edge of \emptyset_1 .

SYNC

This output line is provided to identify those cycles in which the microprocessor is doing an OP CODE fetch. The SYNC line goes high during \emptyset_1 of an OP CODE fetch and stays high for the remainder of that cycle. If the RDY line is pulled low during the \emptyset_1 clock pulse in which SYNC went high, the processor will stop in its current state and will remain in the state until the RDY line goes high. In this manner, the SYNC signal can be used to control RDY to cause single instruction execution.

Memory Management Control (Po-P3)

The four extended address pins, Po-P3, enable the processor to align to one of sixteen banks of 64K memory space. The use of the instructions; Load A indirect Y (B1₁₆) and Store A indirect Y (91₁₆), transfers the processor from the normal execute mode to the indirect mode. In the execute mode, the processor is aligned to a particular memory bank. The indirect mode aligns the processor to a predetermined memory block. The contents of the extended address registers is controlled by software with the execute register at location 0000 and indirect register at 0001.

During fetch and execution of the indirect mode instructions, the processor remains in execute mode until data transfer is to occur. At this time the processor switches to the indirect mode aligning itself to the new memory block. After one cycle the processor returns to the execute mode.

The upper four bits of the data bus are logic "0"s during a read/write to the extended address registers. Also, these registers are set to logic "1"s during reset.

The extended address pins are not under control of AEC and are not tri-statable.

ADDRESSING MODES

Accumulator Addressing

This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

Immediate Addressing

In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

Absolute Addressing

In absolute addressing, the second byte of the instruction specified the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

Zero Page Addressing

The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

Indexed Zero Page Addressing

(X, Y indexing). This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

Indexed Absolute Addressing

(X, Y indexing). This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time.

Implied Addressing

In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

Relative Addressing

Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to +127 bytes from the next instruction.

Indexed Indirect Addressing

In indexed indirect addressing (referred to as [Indirect, X]), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

Indirect Indexed Addressing

In indirect indexed addressing (referred to as [Indirect. Y]), the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

Absolute Indirect

The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

INSTRUCTION SET—ALPHABETIC SEQUENCE

BEC Branch on Carry Clear BEC Branch on Carry Set BEC Branch on Result Zero BIT Test Bits in Memory with Accumulator BMI Branch on Result Minus BNE Branch on Result Minus BNE Branch on Result Minus BNE Branch on Result Plus BRK Force Break BVC Branch on Overflow Clear BVC Branch on Overflow Set BVC Branch on But Item Push Processor Status on Stack BVC Branch on Besult Plus BVC Branch on Bit Right (Memory on Stack BVC Branch on Besult Plus BVA Branch on Bves Location BVA Branch on Besult Plus BVA Branch on Besult	ADC AND ASL	Add Memory to Accumulator with Carry "AND" Memory with Accumulator Shift Left One Bit (Memory or Accumulator)	LDA LDX	Load Accumulator with Memory Load Index X with Memory
BIT Test Bits in Memory with Accumulator BMI Branch on Result Minus BNE Branch on Result Minus on Stack BNE Branch on Result Minus BNE Branch on Re	BCS	Branch on Carry Clear	LDY LSR	Load Index Y with Memory
BMI Branch on Result Minus BNE Branch on Result Into Zero BPL Branch on Result Plus BRK Force Break BVC Branch on Overflow Clear BVS Branch on Overflow Set CLC Clear Carry Flag CLD Clear Decimal Mode CLI Clear Interrupt Disable Bit CLV Clear Overflow Flag CMP Compare Memory and Index X CPY Decrement Index X by One DEC Decrement Index X by One EOR TSX Increment Memory by One INC Increment Index X by One INC Increment Index X by One Inc		Branch on Result Zero	· - ·	No Operation
BRICE Branch on Result not Zero BPL Branch on Result Plus BRK Force Break BVC Branch on Overflow Clear BVC Branch on Overflow Set Branch on Result not Zet Branch on Result not Stack Brull Rocumulator (Memory or Accumulator) Brate One Bit Lett (Memory or Accumulator on Stack Brate One Bit Lett (Memory or Accumulator) Brate One Bit Lett (Memory or Accumulator) Brate One Bit Lett (Memory or Accumulator on Stack Broth Accumulator on Stack Brate One Bit Lett (Memory or Accumulator on Stack Broth Accumulator on Stack Brate One Bit Lett (Memory or Accumulator on Stack Broth Accumulator on Stack Brate One Bit Lett (Memory or Accumulator on Stack Broth Accumulator on Stack Broth Accumulator on Stack Brate One Bit Lett (Memory or Accumulator) Brate One Bit Lett (Memory or Accumulator) Brate One Bit Lett (Mem	ВМІ	Didiich on Hesult Minus		"OR" Memory with Accumulator
CLC Clear Carry Fiag CLD Clear Decimal Mode CLI Clear Overflow Fiag CLV Clear Overflow Fiag CMP Compare Memory and Accumulator CPX Compare Memory and Index X CPY Compare Memory Index X CPY Compare Memory Decrement Index X D CPY Compare Memory by One CPY Compare Memory and Index X CPY Compare Memory and Index X CPY Compare Memory Index Index X CPY Compare Mem	BPL BRK BVC	Branch on Result not Zero Branch on Result Plus Force Break Branch on Overflow Clear	PHP PLA PLP	Push Processor Status on Stack Pull Accumulator from Stack Pull Processor Status from Stack
CMP Compare Memory and Accumulator CPX Compare Memory and Index X CPY Compare Memory and Index X SEC Set Carry Flag Set Decimal Mode Set Dec	CFD CFD CFC	Clear Carry Flag Clear Decimal Mode Clear Interrupt Disable Bit	RÓR RTI RTS	Return from Interrupt
DEC Decrement Memory by One Decrement Index X by One Decrement Index X by One STX Store Index X in Memory Decrement Index Y by One STY Store Index Y in Memory Decrement Index Y by One STY Store Index Y in Memory Decrement Index Y by One STY Store Index Y in Memory Store Index Y in Memory Store Index Y in Memory Decrement Index Y by One STX Transfer Accumulator to Index X Transfer Accumulator to Index Y INX Increment Index X by One STX Transfer Index X to Accumulator Index X increment Index Y by One STX Transfer Index X to Accumulator Transfer Index X to Stack Register STYA Transfer Index X to Accumulator Stark Provinces Transfer Index X to Accumulator Stark Prov	CMP CPX CPY	Compare Memory and Accumulator Compare Memory and Index Y	SEC SED	Set Decimal Mode
EOR Exclusive-or Memory with Accumulator TAX Transfer Accumulator to Index X INC Increment Memory by One TSX Transfer Accumulator to Index Y INX Increment Index X by One TSX Transfer Slack Pointer to Index X INY Increment Index Y by One TXA Transfer Index X to Accumulator INY Jump to New Location TYA Transfer Index X to Stack Register TYA Transfer Index X to Accumulator TYA Transfer Index X to Accumulator TYA Transfer Index X to Accumulator	DEX	Decrement Memory by One Decrement Index X by One	STX	Store Accumulator in Memory Store Index X in Memory
INC Increment Memory by One TSX Transfer Slack Pointer to Index Y Indicate Index X by One TSX Transfer Slack Pointer to Index X Increment Index X by One TXA Transfer Index X to Accumulator TXS Transfer Index X to Stack Register TYA Transfer Index X to Stack Register TYA Transfer Index X to Accumulator TYA Transfer In		"Exclusive-or" Memory with Accumulator		Transfer Accumulator to Index Y
JMP Jump to New Location TYA Transfer Index X to Stack Register	INX ·	Increment Memory by One Increment Index X by One	TSX TXA	Transfer Stack Pointer to Index X Transfer Index X to Accumulator
				Transfer Index Y to Accumulator

PROGRAMMING MODEL



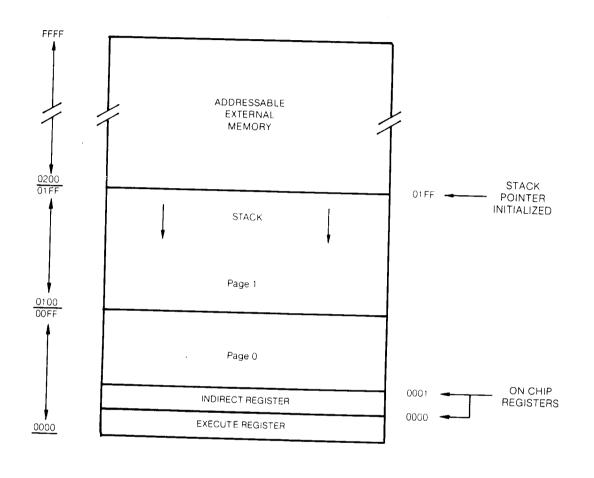
INSTRUCTION SET — OP CODES, Execution Time, Memory Requirements

				INSTRUCTIONS		1800	REDIAT	E	A8300	NJE.	ZF	RO PA	GF .	r	CUM.	_	MPLI	En	-	NO. X	, 7		~ -	Τ.			7		_	_			,			_						,					
	MNEN	ON K		OPERATION		CP	NI		PN													(39)	O). Y	+	PAG	E, X	1	ABS.	<u> </u>	L	.20A	Y	R	ELAT	VE.	1		ECT	Z	. PAG	E Y	C	ONE	Ш)N (CODI	ES
A	C)	С	$A + M + C \rightarrow A$					D 4		GE	2	-	0"	N :	10	1N	4	CP!		= (OP.	7 =	C	N	=	Ŭ₽.	1	=	ಿ	١,٠١	=	OР	N	Ħ	OF) r.	12	CF	P.	=	٠,	7	C	ı	Э	V
4	N	i	٥	A A M → A	.1	29	2	2 2	E 4	13	25	2	2	-	-		i		61			7	5 2	7:	4	2	70	4	3	79	4	3			Г		Τ		1	Т	П	,	٠	٠	-	_	
2	S			C + 7 0 + 0					E 6					اده	٠,	-			21	6	4	3:	5 2	35	5 4	12	30	4	3	39	4	3										١.	٠	-	-	_	-
8	С	;	Ç	BRANCH ON C = Ø	-2-	П		ľ	"	Ľ		1	-	-	٠ '	İ				İ	Ì			16	6	12	.€	-	3			İ	l					ļ		İ		٠	٠	,	-	-	-
В	С	:	S	BRANCH ON C = 1	:2:					-				ı	İ					ı	- 1	i										ŧ .	00	1	5							-	-	-	-		-
E	£		2	BPANCH ON Z = 1	2.	\vdash	\dashv	+	+	╁	\vdash	+	+	+	+-	╁	+	-	-	\dashv	-+		+	+	+	ـ	Ļ	Ļ.,	_			_	80	_		L	\perp	4_	╀	┖	_	-	_	-	_	-	-
3	- 1		T	A a M		H		2	3	12	24	3	2	1		1						ĺ					1						FØ	2	2					1		-	-	-	-	-	-
F	Ų	1		BRANCH ON N= 1	2					Ĭ.	-		-	ļ	Į				Ì	1		1	1									١,		ĺ							ŀ	1,15	٠	-	-	-	Ma
9	N		Ε	BRANCH ON Z + @	-2		1	ı	1			İ	-							- 1	-												30		ĺ			İ		1	١.		-	-	-	-	-
₽	٥		-	BRANCH ON N = 9	-2										-		1		- 1			-			1	į .				ļ	i		DØ.	i	ı					ŀ		-	-	-		-	-
=	77		4			1	\top	+	╁			-	\dashv	+	+	00	-	-	-+	+		+	+	+	+	├	Н					_	.6	2	2	Ļ	╀	Ļ	╄	ļ.,				-		_	_
9	V		2	BRANCH ON V = 0	-2				1				1	ļ		100			- [- 1	ľ	- [1	1				ı										Ì		-	-	-	1	-	-
8	٠		S	BRANCH ON VISIT	2:				1			- 1	- 1			İ	ÌΙ			- 1	- 1		1									i	50		1				i	ļ	i		-	-	-	-	-
ĵ.			2	2 → ○		- }					- 1		- [12	2	,	- 1	- 1									i		i		7€	2	2		1					-	-	-	-	-	-
- 3			5	0 → 0		- 1			ļ	l i	- [-		- [D8	l i		- !		ı		İ			Ι.		li		- 1			·					1					-	0	-	-	-
2	-			∂ → ·		\dashv	\top	+	†	Н	+	\pm	-+	+	+-	58	_	7	+		+	+	+	+	⊢	\vdash		-	!	- ∔	4		-			_	L	\vdash	Ļ	L_			_	-	-	9	-
0	L		7	0 → ✓								- 1			1	88								-					- 1	ļ							1	İ		l		-	-	-	Ů	-	-
0	*,*		2	A = M		cə :	2 2	c	1	3	C5	3 :	2		-	1			-,	اء	,	. .	2	1	١.	,	5.	. 1	_			.	- 1				1					~	-		-	-	0
-	Đ		×	x = 1.1					4					- 1				ľ		<u> </u>	ٔ ا	1	-	103	-	-	00	*	-		1	3						ĺ			۱ ۱	٠	٠	٠	-		-
÷.	-		Ÿ	Y - M		cəl :	2 2	cc	: 4	3	C4	: 1:	3							- }				i			li	1	-	ł			- 1				ļ			١.		٠	٠	٠		-	-
-	ξ		1	₩ = 1 → ₩		T		CE	é	3 1	26	: 1.	: 1	T	+-	T		1	+	-+	+	+	╁╌	r's	6	1	ΩE	-	7	\dashv	-	-+		4		_	⊢	⊢	├		\vdash	<u>. </u>	٠.	٠	-		_
D	Ε		'	$x = 1 \rightarrow x$			ļ				- 1	-				CA	2	.		-				100	ľ.	•		Ì			İ	i	İ									٠	•	-	-	~	-
0	E		*	← 1 → r				İ					1			88	2	,		- 1			İ					ļ			-	ļ										•	•	-4	-	-	-
Ē	3		2	$\Delta = M \rightarrow A$	÷, ,	49 3	2	40	1:	3 .	:5	: 1:				li	- 1	- 1	. I.	6 l	- 5	: 5	2	5.5	ا ا	3	5.3	.		50	, [,										٠	•	-	-	-	-
1	Ŋ		3	$M + 1 \rightarrow M$	1			EF	6	3 8	6	s z	: 1										1			2			-	~	1	1			İ							٠	•	-	-	-	-
	*;		١ ١	i - ' → -			T	T		7	\top	T	+	+	+	68	2	1	\top	+	\pm	+	+	۲Ť	-	-	+	+	+	+	\dashv	+	+	\dashv	-	-	-	-	H			<u> </u>	_	_	-		_
1	74		1	Y - ' → '	1	Ì			1 1	- 1			İ		-	ca.	2	,			ı		1	ĺ				- 1		- [1	-		Ì	- [ıl	Į			/	-	-	-	-
Ĵ.	1,1		2	JUMP TO NEW LOC				‡C	2	3		į						1									1		-		-		İ			60	5	3		ĺ	- 1	•	/	-	-	-	-
J	8		۹	JUMP SUB	- 1			20	6	3					1								1			Ì				1						00	١	J	П	-	-	-	-	-	-	-	*
į.			۵	*.4 → A	11 2	:012	12	AD	:	3 4	١ ج	: [:	. [12	1/6	; l :	. 6	٠ د	2	85	۱, ۱	2	ar [.			,	3										_	-	-	-		-

				_			_					_																												•						
	NEMO	NIC	ODERLYNN		MMEDIA	-		LUTE	+	ZERO	-	-	ACCUR	_		PLIE		•	0. X			Ot 4		Z PAE			ABS.			284	Y	RE	LATI	VE	9	NDIRE	act .	1.	PAG	ΕY]	CON	DIT	MON	CO	DES
	CMU		OPERATION	- 12	4	_)P 1	_		_	=	ÇP	1	z,	;₽	٠,	n (P	.1	# F.	0	1 2	0	P :	1 3	ं	1.	3	;p	1:		70	٠, ا	=	OF	71	T _E	loe.	1.	=	1.	- 2	-	-		
1		•		Ä.	1 - 1	- 1	÷Ε ·	- 1 '		- 1						٦		T	٦	\top	T		T	T	1	T	T	ī	8£	1	3			\vdash	T	t	•	B6	-	-						
-	2	r R	M → Y	ÄE	1 3		1	- 1 '		4 3										- 1	ı		rò	4 4	2	50	. 4	3		ļ		-				İ		ŀ							_	
	S		0 → 7 O → C	Ì		- [-	E .	5	-11	5 5	2	4.0	-	•	i	i	İ				ı		5	6 6	12	5E	1.	ī		Ì		- 1	ı						İ		la				_	_
1.	0		NO OPERATION				İ	ĺ							E٩	2	,		1													ĺ							l			_	Ĺ			
-	Fi		$A \neq M \rightarrow A$	_	2	3 2	ic -	: :	J:	3	10	Ĺ				-1	- le	,· .	e	: ·		5 2		:	2	1.0	1 4	3	19	4	3	ı				1										
i	~	4	A → M _S S - 1 → S						Ī	Г	Γ	П			48	3	1		T	T	T		1	1-	T	1	i	+			\dashv		Τİ	H		\vdash	Н	<u> </u>	1	+	+	÷	_	-		
3	H	D	P→'ts S-:→S				ı				İ]		85	3	1		1									1			- 1	- 1	- 1			ļ				ļ						
٩	Ļ	4	S - ' → S M _S → :			- 1					ĺ			- 1	68	4	1			1	ĺ		İ			i			ı																•	_
P	L	=	1			-	1	1				!		- 1	29	.1			-	1	1		1	ľ	1			1			-	1		ļ							,	,	ce		RED	
H-	0	-	1 0+C+			2	ŧΓ	3	2.6	5	1.:	P.A.					- {			i	İ		136	16	12	3E	-	1				- 1	- 1				П				l.					
	Ĵ	=	-C1-7 01-1	T	П	-	E d	1.3	-66	-	10				寸	+	+	i	+	Ť	+	Ť		16	-	+	-	3		-	-	\dashv	+			H	╁	Н	⊢	╀	1			_	_	_
R	Т		RTRN INT		1	1								ı.	101	6	, [-				1	1		1			- 1								ļ		1	,			RED	_
1 2	-	č	ATAN SUB	1		-		j			ŀ			ı,	30	a	.		1	-	1		1	1	1					- 1	- [-					1				(H	ES	Ю	4ED	
S	G	S	$A - M = C \rightarrow A$ 1.	€9	2 .	3 E	cl :	3	E f	3	10			- 1	İ		F	1 6	ı İ.	10	. _	2	FS	١,	,	EO.	4	,	Eal	.	,	í	- 1	1	- 1		П				-	-	_		-	_
S	Ē	С	1 → 0					1		j				1:	8	2	, [ľ	1	1		1				-	1	1		- [. 1			•	٠	. 3	-	-	٠
S	Ε	C	1 → D						1					- 1	·a :	- 1	.			-		1									Ţ	- 1	-	- 1	- 1		П	H			l T	_	,			-
S	£		· - ·			T	+-	$^{+}$	1	f			-j	-+-	8 .	-	,		+	+	÷	+	╁		1	-		-	-+	-	-+	+	+		\dashv	Н	\vdash	-	_					_		
S	Ţ	4	A → M			80	1	3	85	3	2			- [ı	2	ء ا ۽	1:	g.	18	-	35	4	3	00		3	30	5	,	-		1	ľ			.			Ī	_	_		-	-
5	*	•	. → M			86	4	2	86	3	2								ı	1	1	1	1		1	1			-		١,	1		-				96		ا ؞ ا	i -	-	-	-	-	-
\$	7		Y → M	П		30	1	13	84	3	-	- 1	- 1		- 1			1					94		2	ĺ			- 1				- 1	ı	- [ľ	e.	4		-	_	-	-	-	-
T	4	•	$7 \rightarrow \bar{x}$				1		1	Ι,			- [1.	ء ا م	, ,	,		-		ĺ		1		ľ	i		-	- 1					- 1				- 1			ı .	-	-	-	-	~
-	ů.	,	4 -> 4			1		\vdash				T	7	-	8 2	+		+	+	t	╁	+	-	\vdash	-			-	+	\dashv	+	+	+	+	\dashv	-		\dashv	_		<u>. </u>	<u>. </u>	-	_	_	
•	3		3 → ‹	\perp							- 1	- 1			A S	- 1	.			1				j		l		- 1		1	- [-	İ	-	-						•	,	-	-	-	-
-	•	ı	1 -> û					İ	١.		Ì			- 1	Ala	- 1		İ	i				ļ	ĺ.,										-1		İ	i				•	•		-	-	-
-	٠.	S	v → 3				1					ı	-	- 1	A 3								i				j			1		1	-		-	-	ı	ł			٠	٠	-	-	-	-
-	v	4	·			1					- 1	- 1		9		- 1												1	- {					- [-	-			-	-	-	-	-	-
- 1-	i.c	2 + 70	" IF FAGE BOUNDAY IS CROSSE	_		-		1		<u>'</u>		!		10	- 1 -	Τ.	<u>.</u>		1.	4_	_	<u>!</u>	<u></u>	-					_!		1	_!		_!				!			<u>. </u>	<u>. </u>	_	_	-	-
-21	ن د	g •	* F SRANCH COCURS TO SAME	D DAG	E			*			EX X											٠		00						7				νE C	CR			٠.				rCLI				
31	40	0.075	". F BRANCH CCCURS TO SAME "I IF BRANCH CCCURS TO DIFFE	=E-7	T=AG	Ε		Δ					TOR									÷		uBT ND	**	•			•	•		on or i						==		C	. 8	*TE3	ŝ			
3			CT-BORROW MBL MODE Z FLAG IS INVALID					1,1					en e		STA.	E 4(COP	ESS						P.						j.				DIF.E												į
	4C	ต่ะเห็ว	AME MODE 2 FEAG IS INVACID LATOR MUST BE CHECKED FOR ZEA	RO R	ESUL'	7		1,4					ER 5										-								ij,															

Note: Commodore Semiconductor Group cannot assume hability for the use of undefined CP Codes

6509 MEMORY MAP



COMMODORE SEMICONDUCTOR GROUP reserves the right to make changes to any products herein to improve reliability, function or design. COMMODORE SEMICONDUCTOR GROUP does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights nor the rights of others.